**Preferred Device** 

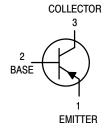
# **One Watt Amplifier Transistor**

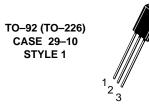
### **PNP Silicon**



### ON Semiconductor™

#### http://onsemi.com





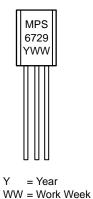
#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	-80	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	-80	Vdc
Emitter-Base Voltage	VEBO	-4.0	Vdc
Collector Current – Continuous	IC	-500	mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	PD	1.0 8.0	Watt mW/°C
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	2.5 20	Watts mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	–55 to +150	°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	125	°C/W
Thermal Resistance, Junction to Case	R <sub>θ</sub> JC	50	°C/W

#### **MARKING DIAGRAM**



#### **ORDERING INFORMATION**

Device	Package	Shipping
MPS6729	TO-92	Bulk

**Preferred** devices are recommended choices for future use and best overall value.

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS			•	•
Collector–Emitter Breakdown Voltage (Note 1.) (I <sub>C</sub> = -1.0 mAdc, I <sub>B</sub> = 0)	V(BR)CEO	-80	_	Vdc
Collector–Base Breakdown Voltage (IC = 0.1 mA, IE = 0)	V(BR)CBO	-80	_	Vdc
Emitter–Base Breakdown Voltage (I <sub>E</sub> = -10 μAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	-5.0	_	Vdc
Collector Cutoff Current (V <sub>CB</sub> = -60 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	-	-0.1	μAdc
Emitter Cutoff Current (VEB = -5.0 Vdc, IC = 0)	lEBO	-	-10	μAdc
ON CHARACTERISTICS (Note 1.)				
DC Current Gain (IC = $-50$ mAdc, VCE = $-1.0$ Vdc) (IC = $-250$ mAdc, VCE = $-1.0$ Vdc)	hFE	80 50	_ 250	-
Collector–Emitter Saturation Voltage (IC = -250 mAdc, IB = -10 mAdc)	VCE(sat)	_	-0.5	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = -250 mAdc, V <sub>CE</sub> = -1.0 Vdc)	V <sub>BE</sub> (on)	_	-1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS	·			
Collector–Base Capacitance (V <sub>CB</sub> = -10 Vdc, f = 1.0 MHz)	C <sub>cb</sub>	-	30	pF
Small–Signal Current Gain (I <sub>C</sub> = 200 mA, V <sub>CE</sub> = 5.0 V, f = 20 MHz)	h <sub>fe</sub>	2.5	25	

<sup>1.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu s,$  Duty Cycle  $\leq$  2.0%.

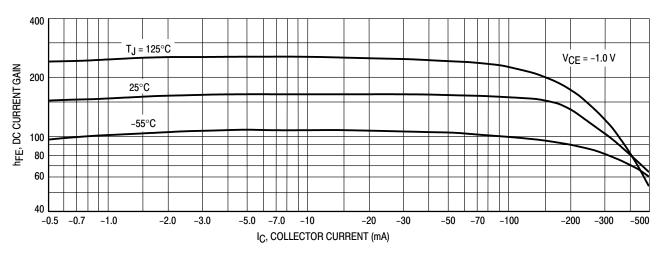


Figure 1. DC Current Gain

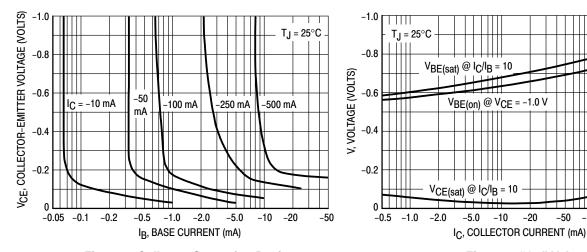


Figure 2. Collector Saturation Region

Figure 3. "On" Voltages

-50 -100 -200

-500

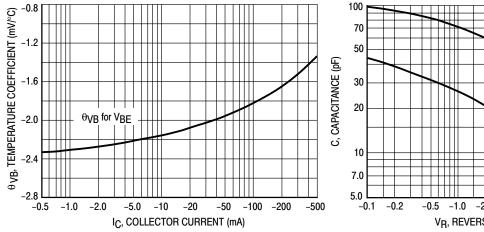


Figure 4. Base–Emitter Temperature Coefficient

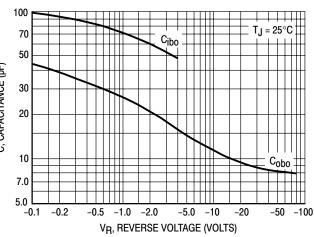


Figure 5. Capacitance

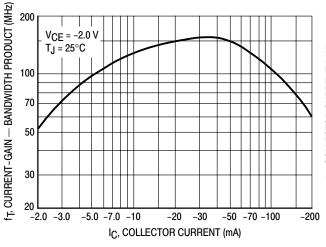


Figure 6. Current-Gain - Bandwidth Product

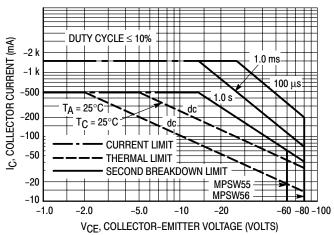
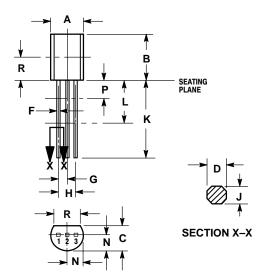


Figure 7. Active Region – Safe Operating Area

#### **PACKAGE DIMENSIONS**

# **TO-92 (TO-226)** CASE 29-10 ISSUE AL



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. CONTOUL OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
  4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSIONS D AND J APPLY BETWEEN L AND K MIMIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.44	5.21
В	0.290	0.310	7.37	7.87
С	0.125	0.165	3.18	4.19
D	0.018	0.021	0.457	0.533
F	0.016	0.019	0.407	0.482
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.018	0.024	0.46	0.61
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0 135		3 43	

- STYLE 1:
  PIN 1. EMITTER
  2. BASE
  3. COLLECTOR

# **Notes**

# **Notes**

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